

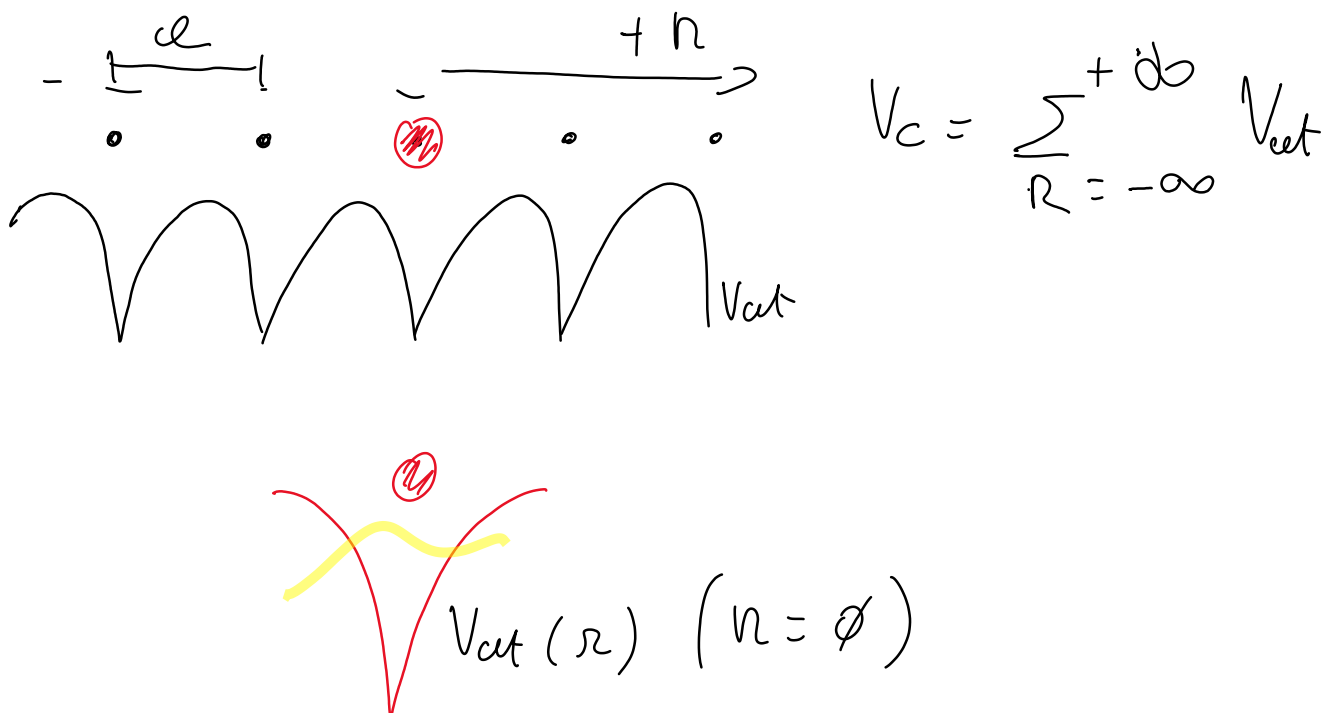
## Tight Binding method for 1D atomic chain

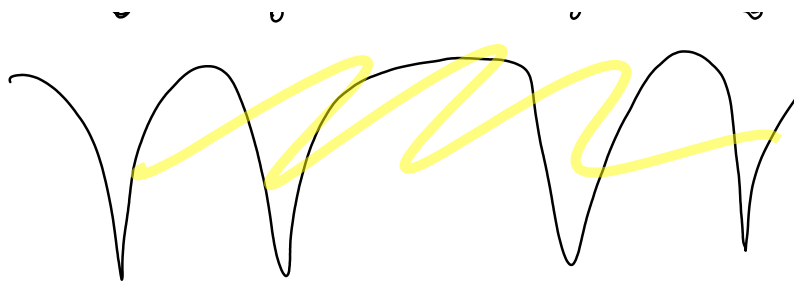
- LCAO for a periodic atomic chain: the Tight Binding method
- s- and p-orbitals overlap integral: relation with band curvature
- overlap integral and bandwidth
- overlap integral and interatomic distance

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$$\Delta U = \begin{cases} \leq & V_{\text{at}} \\ n \neq 0 \end{cases}$$

$$H = T + \underbrace{V_{\text{at}}(r)}_{V_L} + \Delta U$$

$$(T + V_{\text{at}}(r)) \phi$$

$$R = \text{LATTICE}$$

$$\psi = \sum_{n=-\infty}^{+\infty} e^{i k n} \phi_S(r-n)$$

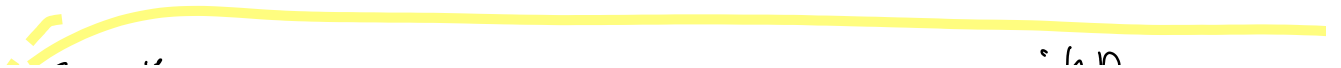
$$R = \text{COMB}, \quad V_A R / A$$

$$\boxed{\psi(r+n) = e^{i k n} \psi(r)}$$

$$\psi = \phi_S(r) + \sum_{n \neq 0} e^{i k n} \phi_S(r-n)$$

$$(T + V_{\text{at}}(r) + \Delta U) \left( \phi_S(r) + \sum_{n \neq 0} e^{i k n} \phi_S(r-n) \right)$$

$$E(k) \left( \phi_S(r) + \sum_{n \neq 0} e^{i k n} \phi_S(r-n) \right)$$



$$\int \phi_S^*(r) (\underbrace{T + V_0 r}_{\text{||}} + \underbrace{\Delta V}_{\text{||}}) (\underbrace{\phi_S(r)}_{\text{||}}) + \sum_{n \neq 0} e^{i n r} \phi_S(r-n)$$

$$\int \phi_S^*(r) \underbrace{E(n)}_{\text{||}} (\underbrace{\phi_S(r)}_{\text{||}}) + \sum_{n \neq 0} e^{i n r} \phi_S(r-n)$$

$$\int \phi_S^* (T + V_0 r) \phi_S dr = \varepsilon$$

$$(T + V_0 r)$$

$$\int \phi_S^* \Delta V \phi_S dr = -\beta$$

$$\int \phi_S^* (T + V_0 r) \sum_{n \neq 0} e^{i n r} \phi(r-n) dr = \sum_{n \neq 0} \int \phi_S^* (T + V_0 r) \phi(r-n) dr$$

$$= \sum_{n \neq 0} \int \phi_S^*(r-n) (T + V_0 r) \phi_S(r) dr$$

$$= \sum_{n \neq 0} \varepsilon \int \phi_S^*(r-n) \phi_S(r) dr$$

||  
φ

$$(4) \int \phi_S(r) \Delta V \sum_{n \neq 0} e^{i n r} \phi_S(r-n) dr$$

$$\sum_{n \neq 0} e^{i k n} \int \phi_s(r) \Delta V \phi_s(r-n) dr = -J(n)$$

$$\varepsilon - \beta = \sum_{n \neq 0} e^{i k n} J(n) = E(k)$$

$$E(k) = \varepsilon - \beta - \sum_{n \neq 0} e^{i k n} J(n)$$

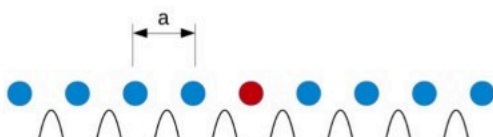
near neighbour interaction  $n = \pm 1$

$$E(k) = \varepsilon - \beta - e^{i k a} J(a) - e^{-i k a} J(a)$$

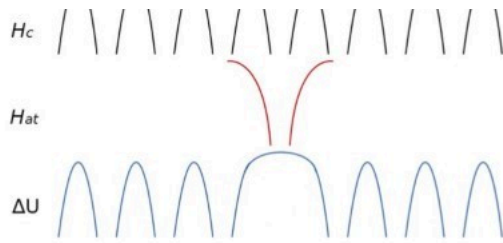
$$E(k) = \varepsilon - \beta - 2J \cos(ka)$$


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Tight-Binding approximation



$$H_{at}(r) \phi_s(r) = \varepsilon_s \phi_s(r)$$



$$H_c \Psi = E \Psi,$$

$$(H_{at}(r) + \Delta U(r)) \Psi = E \Psi.$$

$$\Psi_k(r) = \sum_R \exp(ikR) \phi_s(r - R)$$

$$E(k) = \varepsilon_s - \beta - 2\gamma(a) \cos(ka)$$

$$\approx \varepsilon_s - \beta - 2\gamma(a) \left(1 - \frac{1}{2}(ka)^2\right)$$

$$= \varepsilon_s - \beta - 2\gamma(a) + \gamma(a)(ka)^2$$

$$ka \ll \pi \quad k \rightarrow 0$$

$$\cos(ka) \approx 1 - \frac{1}{2}(ka)^2$$

$$\gamma > 0 \quad \text{s-STATES}$$

$$\gamma < 0 \quad \text{p-STATES}$$

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## Comparison with "real" bandstructures

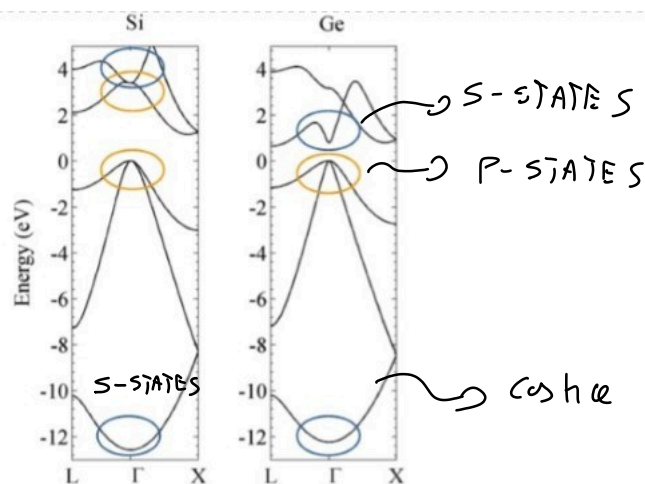


Figure 2.7: Bandstructure of Si and Ge taken from P. Moontragoon et al. J. Appl. Phys 112, 073106 (2012). The curvature of the bands around  $\Gamma$  (i. e.  $k = 0$ ) are highlighted in blue (orange) for bands originating from s-type (p-type) orbitals.

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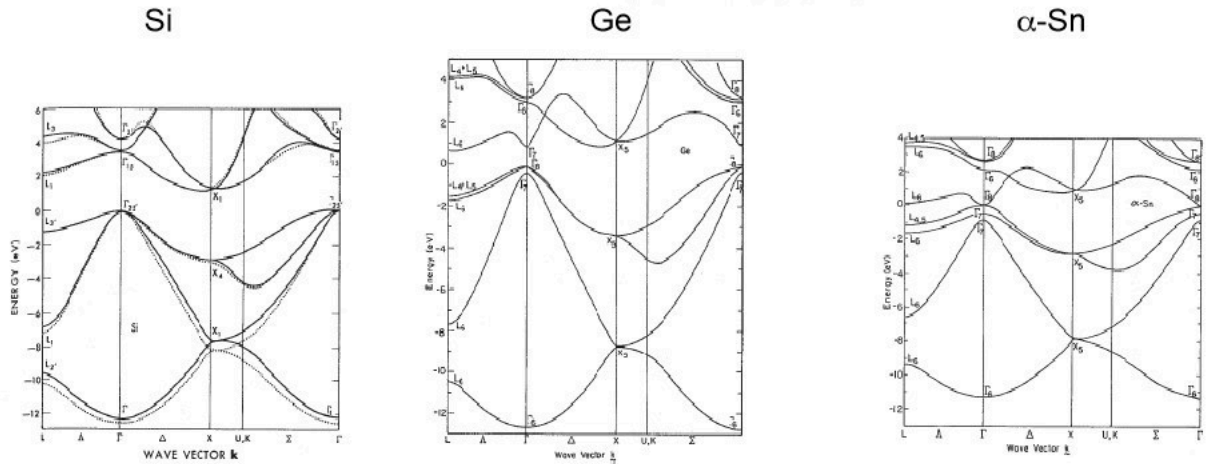
## Comparison with "real" bandstructures

Relationship between the overlap integral  $\gamma$  and the energy width of the band

$$E(k) = \varepsilon_s - \beta - 2\gamma(a) \cos(ka)$$

$$\approx \varepsilon_s - \beta - 2\gamma(a) \left(1 - \frac{1}{2}(ka)^2\right)$$

$$= \varepsilon_s - \beta - 2\gamma(a) + \gamma(a)(ka)^2$$



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## Overlap integral and effective mass

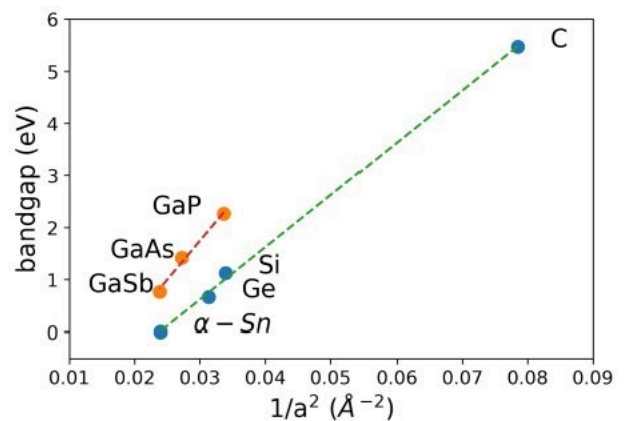
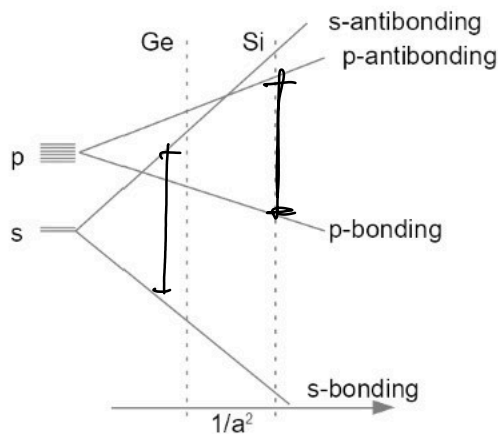
The dispersion around the  $\Gamma$  point ( $k \approx 0$ ) of the Brillouin Zone can be described by means of the effective mass  $m^*$

$$\gamma = \frac{\hbar^2}{2m^*a^2}$$

$$\gamma \propto \frac{1}{a^2}$$

$\int \hbar=0$

$E(k) \quad \gamma \hbar^2 a^2 = \frac{\hbar^2 k^2}{2m^*}$



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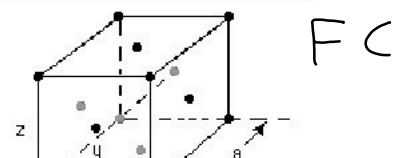
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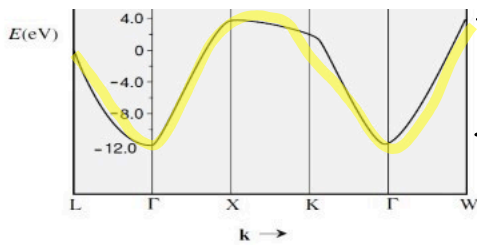
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## Comparison with "real" bandstructures

$\gamma = 1.0 \text{ eV} \quad E_s + \beta = 0$

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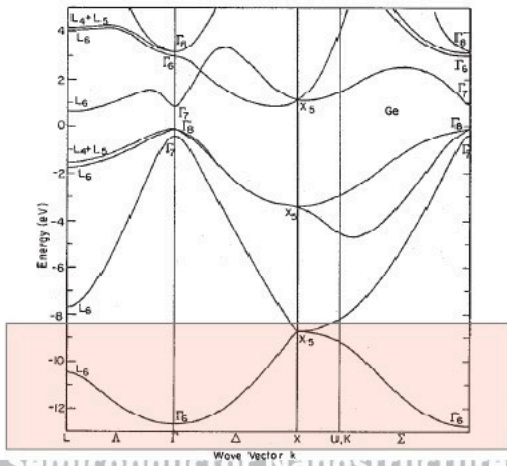


$$E(\mathbf{k}) = E_s - \beta_s - \sum_{\mathbf{R}} \gamma(\mathbf{R}) e^{i\mathbf{k} \cdot \mathbf{R}}$$

For  $\mathbf{R}$  spanning the first 12 near neighbours in a simple FCC lattice

$$\frac{a}{2}(\pm 1, \pm 1, 0); \frac{a}{2}(\pm 1, 0, \pm 1); \frac{a}{2}(0, \pm 1, \pm 1)$$

$$\begin{aligned} E(\mathbf{k}) &= E_s - \beta_s - \gamma \left[ e^{i(k_x + k_y)a/2} + e^{i(k_x - k_y)a/2} \right. \\ &\quad \left. + e^{i(-k_x + k_y)a/2} + e^{i(k_x - k_y)a/2} + \dots \right] \\ &= E_s - \beta_s - 4\gamma \left[ \cos \frac{k_x a}{2} \cos \frac{k_y a}{2} \right. \\ &\quad \left. + \cos \frac{k_y a}{2} \cos \frac{k_z a}{2} + \cos \frac{k_z a}{2} \cos \frac{k_x a}{2} \right] \end{aligned}$$



S-like bonding band

